

## KT809A Datasheet, Equivalent, Cross Reference Search

Type Designator: KT809A

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation ( $P_c$ ): 50 W

Maximum Collector-Base Voltage  $|V_{cb}|$ : 400 V

Maximum Emitter-Base Voltage  $|V_{eb}|$ : 4 V

Maximum Collector Current  $|I_c \text{ max}|$ : 3 A

Max. Operating Junction Temperature ( $T_j$ ): 150 °C

Transition Frequency ( $f_t$ ): 5 MHz

Collector Capacitance ( $C_c$ ): 150 pF

Forward Current Transfer Ratio ( $h_{FE}$ ), MIN: 15

Noise Figure, dB: -